

MAC97 Series

Preferred Device

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO-92 package which is readily adaptable for use in automatic insertion equipment.

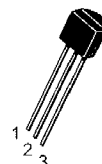
- One-piece, Injection-Molded Package
- Blocking Voltage to 600 Volts
- Sensitive Gate Triggering in Four Trigger Modes (Quadrants) for all possible Combinations of Trigger Sources, and especially for Circuits that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability
- Device Marking: Device Type, e.g., MAC97A4, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (T _J = -40 to +100°C) (Note 1) Sine Wave 50 to 60 Hz, Gate Open MAC97A4 MAC97A6 MAC97-8, MAC97A8	V _{DRM} V _{RRM}	200 400 600	Volts
On-State RMS Current Full Cycle Sine Wave 50 to 60 Hz (T _C = +50°C)	I _{T(RMS)}	0.6	Amp
Peak Non-Repetitive Surge Current One Full Cycle, Sine Wave 60 Hz (T _C = 110°C)	I _{TSM}	8.0	Amps
Circuit Fusing Considerations (t = 8.3 ms)	I ² t	0.26	A ² s
Peak Gate Voltage (t < 2.0 s, T _C = +80°C)	V _{GM}	5.0	Volts
Peak Gate Power (t < 2.0 s, T _C = +80°C)	P _{GM}	5.0	Watts
Average Gate Power (T _C = 80°C, t < 8.3 ms)	P _{G(AV)}	0.1	Watt
Peak Gate Current (t ≤ 2.0 μs, T _C = +80°C)	I _{GM}	1.0	Amp
Operating Junction Temperature Range	T _J	-40 to +100	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

TRIACS 0.8 AMPERE RMS 200 thru 600 VOLTS



TO-92

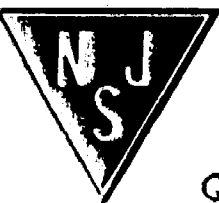
PIN ASSIGNMENT

1	Main Terminal 1
2	Gate
3	Main Terminal 2

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

MAC97 Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	75	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^{\circ}\text{C/W}$
Maximum Lead Temperature for Soldering Purposes for 10 Seconds	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

($T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}$; V_{RRM} ; Gate Open)	I_{DRM} , I_{RRM}	—	—	10	μA
$T_J = 25^{\circ}\text{C}$ $T_J = +110^{\circ}\text{C}$		—	—	100	μA

ON CHARACTERISTICS

Peak On-State Voltage ($I_{TM} = \pm .85\text{ A Peak}$; Pulse Width $\leq 2.0\text{ ms}$, Duty Cycle $\leq 2.0\%$)	V_{TM}	—	—	1.9	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12\text{ Vdc}$, $R_L = 100\text{ Ohms}$) MAC97-8 Device MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	I_{GT}	— — — —	— — — —	10 10 10 10	mA
MAC97A4,A6,A8 Devices MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)		— — — —	— — — —	5.0 5.0 5.0 7.0	
Gate Trigger Voltage (Continuous dc) ($V_D = 12\text{ Vdc}$, $R_L = 100\text{ Ohms}$) MT2(+), G(+) All Types MT2(+), G(-) All Types MT2(-), G(-) All Types MT2(-), G(+) All Types	V_{GT}	— — — —	.66 .77 .84 .88	2.0 2.0 2.0 2.5	Volts
Gate Non-Trigger Voltage ($V_D = 12\text{ V}$, $R_L = 100\text{ Ohms}$, $T_J = 110^{\circ}\text{C}$) All Four Quadrants	V_{GD}	0.1	—	—	Volts
Holding Current ($V_D = 12\text{ Vdc}$, Initiating Current = 200 mA, Gate Open)	I_H	—	1.5	10	mA
Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 1.0\text{ A pk}$, $I_G = 25\text{ mA}$)	t_{gt}	—	2.0	—	μs

DYNAMIC CHARACTERISTICS

Critical Rate-of-Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = .84\text{ A}$, Commutating $di/dt = .3\text{ A/ms}$, Gate Unenergized, $T_C = 50^{\circ}\text{C}$)	$dv/dt(c)$	—	5.0	—	$\text{V}/\mu\text{s}$
Critical Rate of Off-State voltage ($V_D = \text{Rated } V_{DRM}$, $T_C = 110^{\circ}\text{C}$, Gate Open, Exponential Waveform)	dv/dt	—	25	—	$\text{V}/\mu\text{s}$